

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. <b>12007-0074</b>	SERIAL NO. <b>10/580,653</b>
LIST OF REFERENCES CITED BY APPLICANT  (Use several sheets if necessary)		APPLICANT <b>Wolfgang STOLZ et al.</b>	
		FILING DATE <b>03/30/2007</b>	GROUP ART UNIT <b>2826</b>

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
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## FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	<u>TRANSLATION</u> YES NO PART.
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

1.	C. SETIAGUNG et al., "Very Low Threshold Current Density of 1.3 $\mu$ m-range GaInNAsSb/GaNAs 5QWs Lasers", The Furukawa Electric Co., Ltd., Yokohama R&D Laboratories, © 2002, IEEE, pgs. 39-40		
2.	E. GOUARDES et al., "GaInAs-GaInNAs-GaInAs Intermediate Layer Structure for Long Wavelength Lasers", <i>IEEE PHOTONICS TECHNOLOGY LETTERS</i> , vol. 14, No. 7, July 2002, pgs. 896-898		
3.	M. KAWAGUCHI et al., "Photoluminescence and Lasing Characteristics of 1.3 $\mu$ m GaInNAs/GaAsP/GaAs Strain-compensated Quantum Wells", <i>Compound Semiconductors 2003</i> , International Symposium, August 25-27, 2003, pgs. 72-73		
EXAMINER	/Kevin Quinto/	DATE CONSIDERED	07/15/2010
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /KQ/